

FGL60N100BNTD

NPT-Trench IGBT

General Description

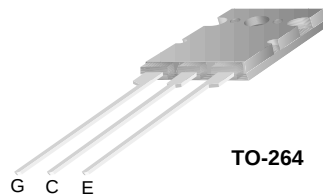
Trench insulated gate bipolar transistors (IGBTs) with NPT technology show outstanding performance in conduction and switching characteristics as well as enhanced avalanche ruggedness. These devices are well suited for Induction Heating (I-H) applications

Features

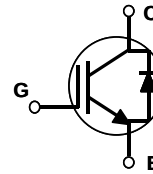
- High Speed Switching
- Low Saturation Voltage : $V_{CE(sat)} = 2.5 \text{ V @ } I_C = 60\text{A}$
- High Input Impedance
- Built-in Fast Recovery Diode

Application

Micro- Wave Oven, I-H Cooker, I-H Jar, Induction Heater, Home Appliance



TO-264



Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Description	FGL60N100BNTD	Units
V_{CES}	Collector-Emitter Voltage	1000	V
V_{GES}	Gate-Emitter Voltage	± 25	V
I_C	Collector Current @ $T_C = 25^\circ\text{C}$	60	A
	Collector Current @ $T_C = 100^\circ\text{C}$	42	A
$I_{CM(1)}$	Pulsed Collector Current	200	A
I_F	Diode Continuous Forward Current @ $T_C = 100^\circ\text{C}$	15	A
I_{FM}	Diode Maximum Forward Current	200	A
P_D	Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$	180	W
	Maximum Power Dissipation @ $T_C = 100^\circ\text{C}$	72	W
T_J	Operating Junction Temperature	-55 to +150	°C
T_{stg}	Storage Temperature Range	-55 to +150	°C
T_L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds	300	°C

Notes :

(1) Repetitive rating : Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}(\text{IGBT})$	Thermal Resistance, Junction-to-Case	--	0.69	°C/W
$R_{\theta JC}(\text{DIODE})$	Thermal Resistance, Junction-to-Case	--	2.08	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	25	°C/W

Electrical Characteristics of IGBT $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
BV_{CES}	Collector Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 1mA$	1000	--	--	V
I_{CES}	Collector Cut-Off Current	$V_{CE} = 1000V, V_{GE} = 0V$	--	--	1.0	mA
I_{GES}	G-E Leakage Current	$V_{GE} = \pm 25, V_{CE} = 0V$	--	--	± 500	nA

On Characteristics

$V_{GE(th)}$	G-E Threshold Voltage	$I_C = 60mA, V_{CE} = V_{GE}$	4.0	5.0	7.0	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C = 10A, V_{GE} = 15V$	--	1.5	1.8	V
		$I_C = 60A, V_{GE} = 15V$	--	2.5	2.9	V

Dynamic Characteristics

C_{ies}	Input Capacitance	$V_{CE}=10V, V_{GE} = 0V,$ $f = 1MHz$	--	6000	--	pF
C_{oes}	Output Capacitance		--	260	--	pF
C_{res}	Reverse Transfer Capacitance		--	200	--	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 600V, I_C = 60A,$ $R_G = 51\Omega, V_{GE}=15V,$ Resistive Load, $T_C = 25^\circ\text{C}$	--	140	--	ns
t_r	Rise Time		--	320	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	630	--	ns
t_f	Fall Time		--	130	250	ns
Q_g	Total Gate Charge	$V_{CE} = 600V, I_C = 60A,$ $V_{GE} = 15V, T_C = 25^\circ\text{C}$	--	275	350	nC
Q_{ge}	Gate-Emitter Charge		--	45	--	nC
Q_{gc}	Gate-Collector Charge		--	95	--	nC

Electrical Characteristics of DIODE $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{FM}	Diode Forward Voltage	$I_F = 15A$	--	1.2	1.7	V
		$I_F = 60A$	--	1.8	2.1	V
t_{rr}	Diode Reverse Recovery Time	$I_F = 60A, di/dt = 20 A/us$	--	1.2	1.5	μs
I_R	Instantaneous Reverse Current	$V_{RRM} = 1000V$	--	0.05	2	μA